

a plurality of first layers made of a nitride semiconductor containing an impurity at a concentration of $1.2 \times 10^{20} \text{ cm}^{-3}$ or more and a plurality of second layers made of a nitride semiconductor containing no impurity, the first and second layers being laminated alternatively on each other and formed on the substrate to form a superlattice structure.

2. (Amended) A buffer as claimed in claim 1 wherein:

a concentration of the impurity contained in a nitride semiconductor for forming said first layer is 10% or less.

3. (Amended) A buffer as claimed in any one of claims 1 and 2 wherein:

said impurity is Si (silicon), C (carbon), Mg (magnesium), or O (oxygen).

4. (Amended) A buffer as claimed in any one of claims 1 and 2 wherein:

a nitride semiconductor for forming said first layer or said second layer is a three-five nitride semiconductor.

5. (Amended) A buffer as claimed in claim 3 wherein:

a nitride semiconductor for forming said first layer or said second layer is a three-five nitride semiconductor.

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6. (Amended) A buffer as claimed in any one of claims 1 and 2 wherein:
said substrate is made from Si (silicon), SiC (silicon carbide), Al₂O₃ (sapphire), or
GaAs (gallium arsenide).

7. (Amended) A buffer as claimed in claim 3 wherein:
said substrate is made from Si (silicon), SiC (silicon carbide), Al₂O₃ (sapphire), or
GaAs (gallium arsenide).

8. (Amended) A buffer as claimed in claim 4 wherein:
said substrate is made from Si (silicon), SiC (silicon carbide), Al₂O₃ (sapphire), or
GaAs (gallium arsenide).

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9. (Amended) A buffer as claimed in claim 5 wherein:
said substrate is made from Si (silicon), SiC (silicon carbide), Al₂O₃ (sapphire), or
GaAs (gallium arsenide).

19. (Amended) A device provided with a buffer, comprising:
said buffer being prepared by forming a device structure on the buffer as claimed in
any one of claims 1 and 2 with the use of a nitride semiconductor as a device material.

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20. (Amended) A device provided with a buffer, comprising:

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said buffer being prepared by forming a device structure on the buffer as claimed in claim 3 with the use of a nitride semiconductor as a device material.

21. (Amended) A device provided with a buffer, comprising:
said low dislocation buffer being prepared by forming a device structure on the buffer as claimed in claim 4 with the use of a nitride semiconductor as a device material.

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22. (Amended) A device provided with a buffer, comprising:
said buffer being prepared by forming a device structure on the buffer as claimed in claim 5 with the use of a nitride semiconductor as a device material.

23. (Amended) A device provided with a buffer as claimed in claim 19 wherein:
a nitride semiconductor that comes to be a device material for constituting said device structure is a three-five nitride semiconductor.

24. (Amended) A device provided with a buffer as claimed in claim 20 wherein:
a nitride semiconductor that comes to be a device material for constituting said device structure is a three-five nitride semiconductor.

25. (Amended) A device provided with a buffer as claimed in claim 21 wherein:

a nitride semiconductor that comes to be a device material for constituting said device structure is a three-five nitride semiconductor.

26. (Amended) A device provided with a buffer as claimed in claim 22 wherein:

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a nitride semiconductor that comes to be a device material for constituting said device structure is a three-five nitride semiconductor.

Please add claim 27 as follows:

27. A buffer as claimed in claim 1, wherein a threading dislocation density is

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substantially equal to $5 \times 10^7 \text{ cm}^{-2}$.